

# NGTB25N120LWG

## IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications. Offering both low on-state voltage and minimal switching loss, the IGBT is well suited for resonant or soft switching applications. Incorporated into the device is a rugged co-packaged free wheeling diode with a low forward voltage.

### Features

- Low Saturation Voltage using Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Low Gate Charge
- 5  $\mu$ s Short-Circuit Capability
- These are Pb-Free Devices

### Typical Applications

- Inverter Welding Machines
- Microwave Ovens
- Industrial Switching
- Motor Control Inverter

### ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	$V_{CES}$	1200	V
Collector current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_C$	50 25	A
Pulsed collector current, $T_{pulse}$ limited by $T_{Jmax}$	$I_{CM}$	200	A
Diode forward current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_F$	50 25	A
Diode pulsed current, $T_{pulse}$ limited by $T_{Jmax}$	$I_{FM}$	200	A
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$P_D$	192 77	W
Short-Circuit Withstand Time $V_{GE} = 15\text{ V}$ , $V_{CE} = 600\text{ V}$ , $T_J \leq 150^\circ\text{C}$	$T_{sc}$	5	$\mu\text{s}$
Operating junction temperature range	$T_J$	-55 to +150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Lead temperature for soldering, 1/8" from case for 5 seconds	$T_{SLD}$	260	$^\circ\text{C}$

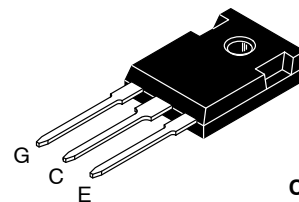
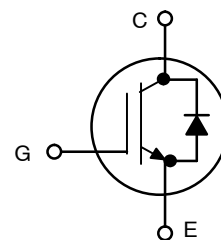
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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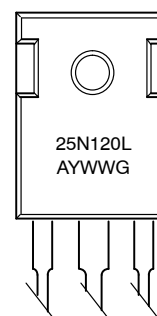
<http://onsemi.com>

**25 A, 1200 V**  
 **$V_{CEsat} = 1.85\text{ V}$**   
 **$E_{off} = 0.8\text{ mJ}$**



**TO-247**  
**CASE 340L**  
**STYLE 4**

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
NGTB25N120LWG	TO-247 (Pb-Free)	30 Units / Rail

# NGTB25N120LWG

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.65	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	1.5	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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### STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	1200	-	-	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 25\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 150^{\circ}\text{C}$	$V_{CEsat}$	-	1.85 2.1	2.3 -	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 250\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 150^{\circ}\text{C}$	$I_{CES}$	-	-	0.5 2.0	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$	-	-	100	nA

### DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$	-	4700	-	pF
Output capacitance		$C_{oes}$	-	155	-	
Reverse transfer capacitance		$C_{res}$	-	100	-	
Gate charge total	$V_{CE} = 600\text{ V}, I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	$Q_g$		200		nC
Gate to emitter charge		$Q_{ge}$		38		
Gate to collector charge		$Q_{gc}$		100		

### SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 25\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$		89		ns
Rise time		$t_r$		29		
Turn-off delay time		$t_{d(off)}$		235		
Fall time		$t_f$		160		mJ
Turn-on switching loss		$E_{on}$		3.4		
Turn-off switching loss		$E_{off}$		0.8		
Turn-on delay time	$T_J = 125^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 25\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$		88		ns
Rise time		$t_r$		29		
Turn-off delay time		$t_{d(off)}$		250		
Fall time		$t_f$		225		mJ
Turn-on switching loss		$E_{on}$		4.4		
Turn-off switching loss		$E_{off}$		1.9		

### DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 25\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 25\text{ A}, T_J = 150^{\circ}\text{C}$	$V_F$		1.7 1.8	1.8	V
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# NGTB25N120LWG

## TYPICAL CHARACTERISTICS

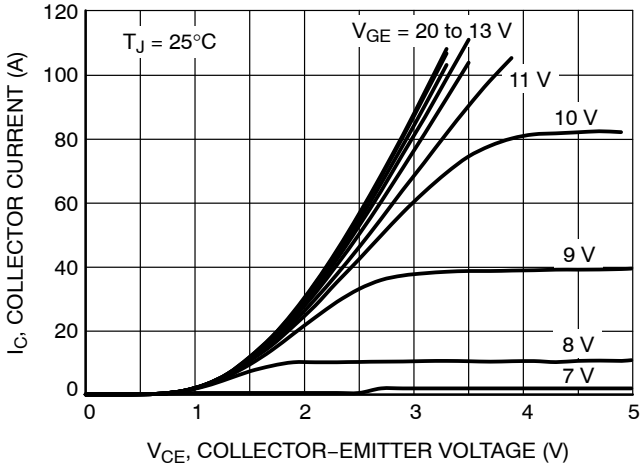


Figure 1. Output Characteristics

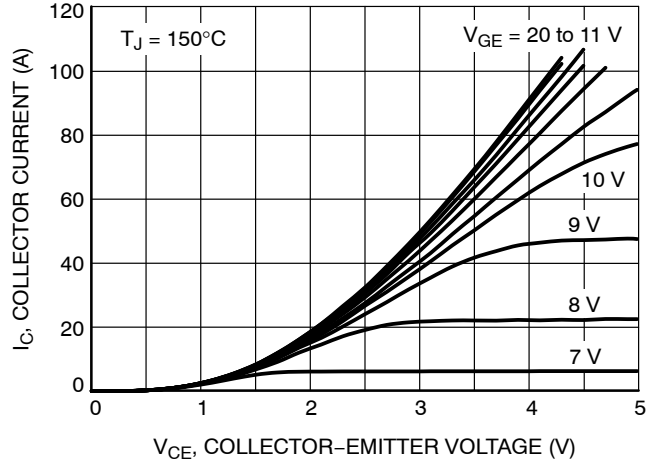


Figure 2. Output Characteristics

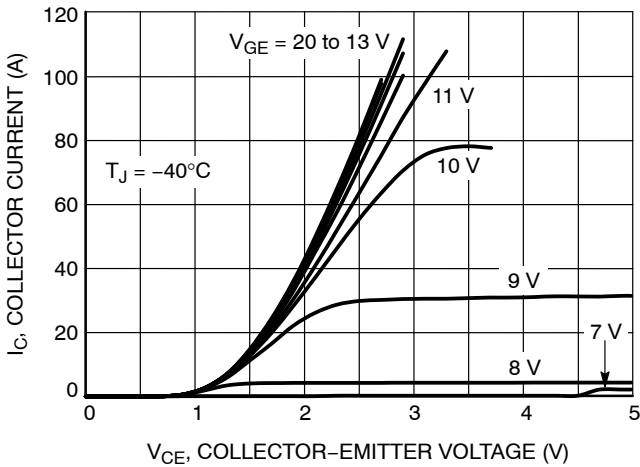


Figure 3. Output Characteristics

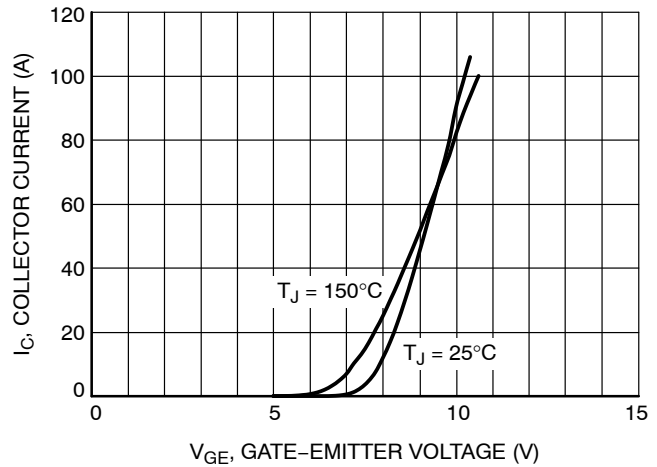


Figure 4. Typical Transfer Characteristics

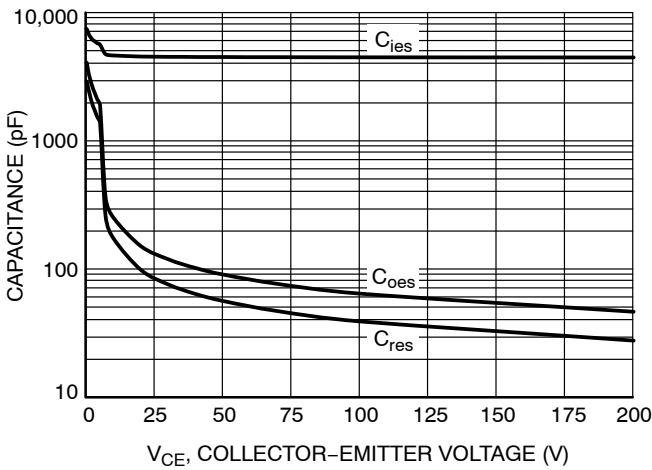


Figure 5. Typical Capacitance

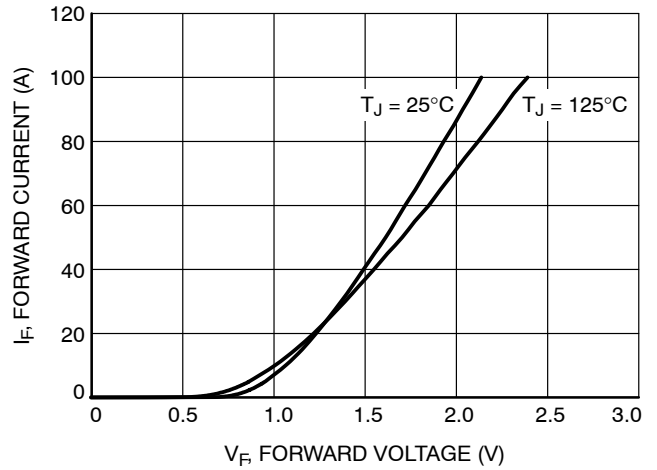


Figure 6. Diode Forward Characteristics

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## TYPICAL CHARACTERISTICS

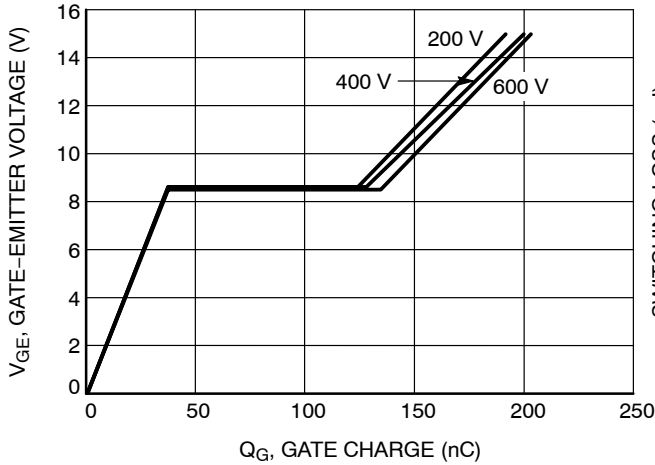


Figure 7. Typical Gate Charge

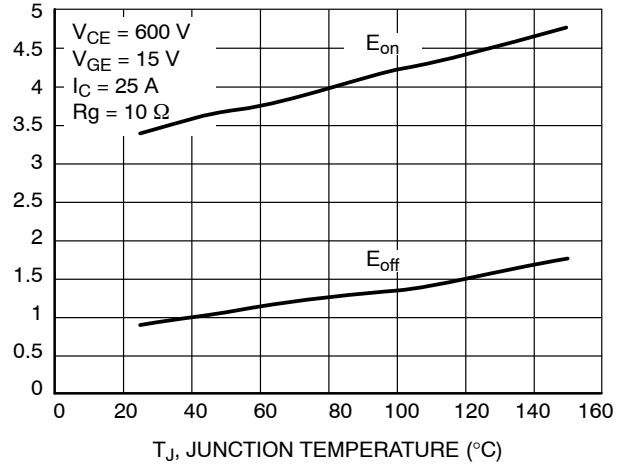


Figure 8. Energy Loss vs. Temperature

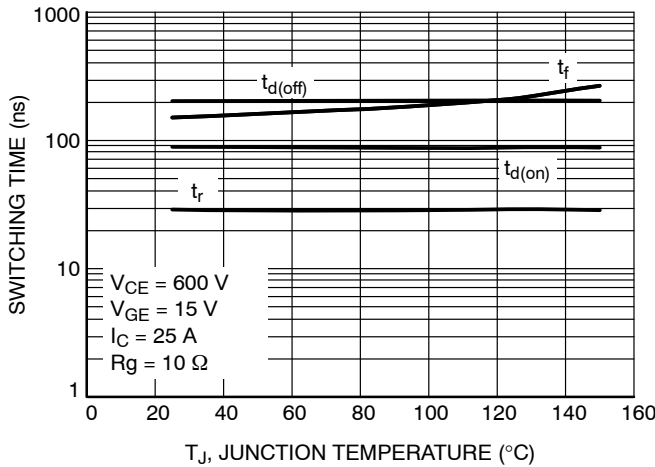


Figure 9. Switching Time vs. Temperature

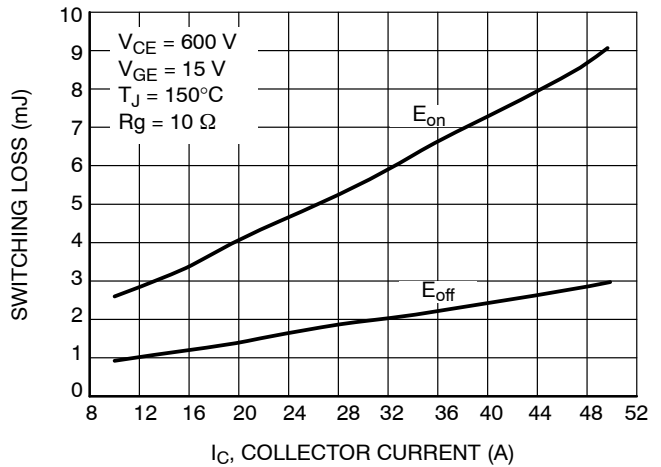


Figure 10. Energy Loss vs.  $I_C$

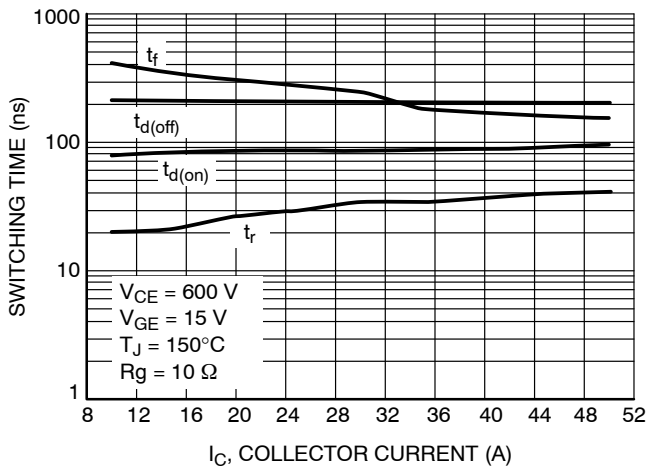


Figure 11. Switching Time vs.  $I_C$

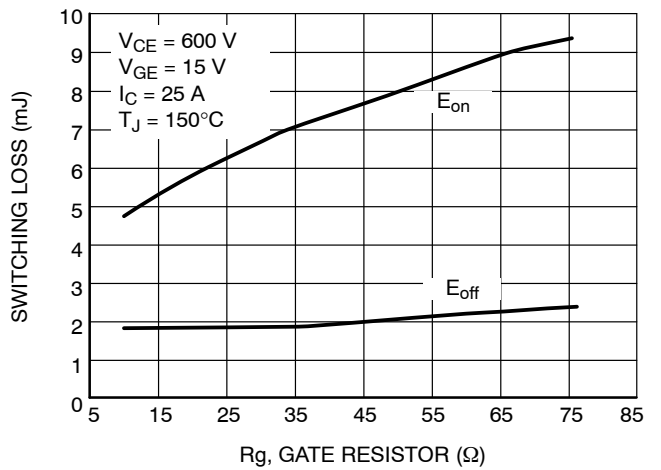


Figure 12. Energy Loss vs.  $R_g$

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## TYPICAL CHARACTERISTICS

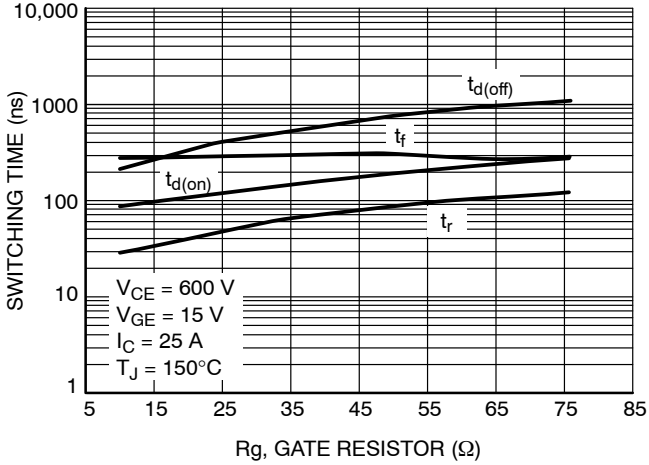


Figure 13. Switching Time vs.  $R_g$

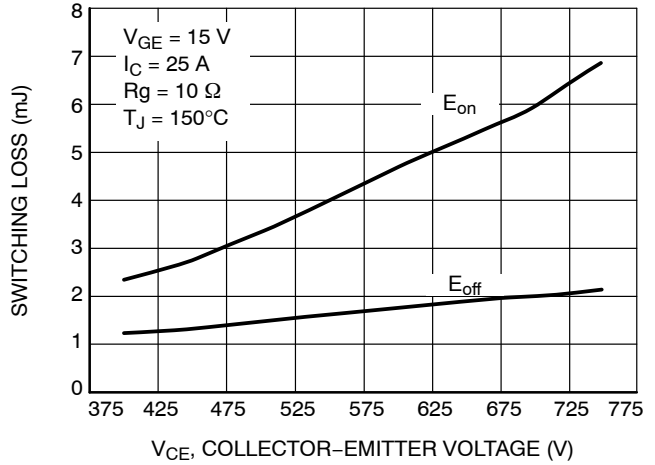


Figure 14. Energy Loss vs.  $V_{CE}$

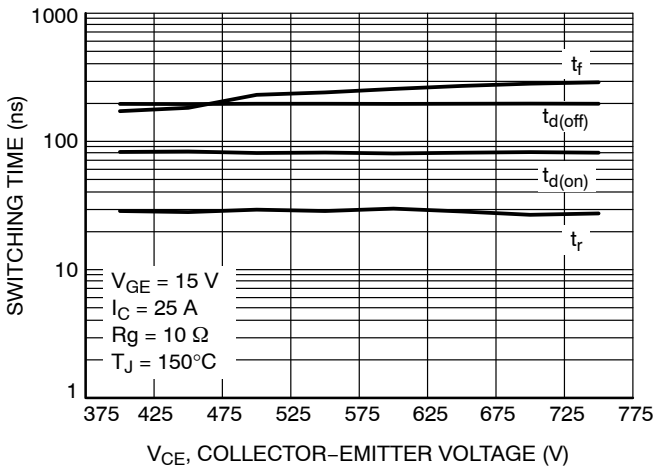


Figure 15. Switching Time vs.  $V_{CE}$

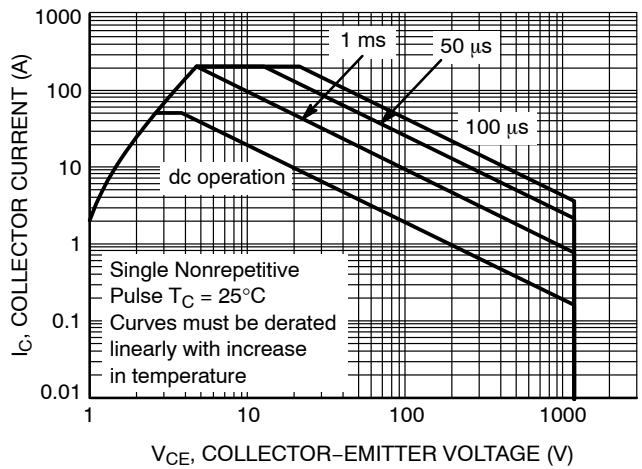


Figure 16. Safe Operating Area

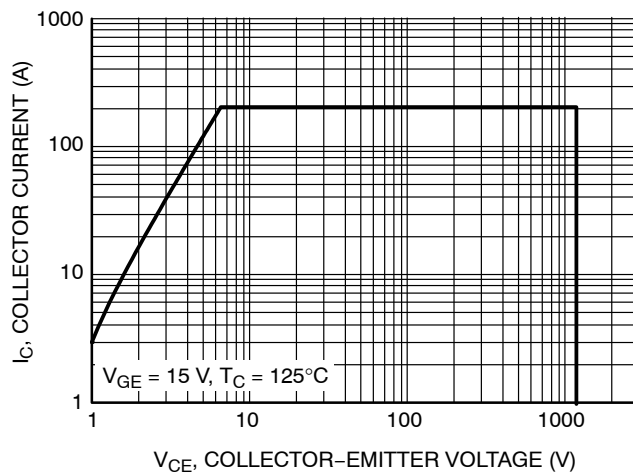


Figure 17. Reverse Bias Safe Operating Area

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## TYPICAL CHARACTERISTICS

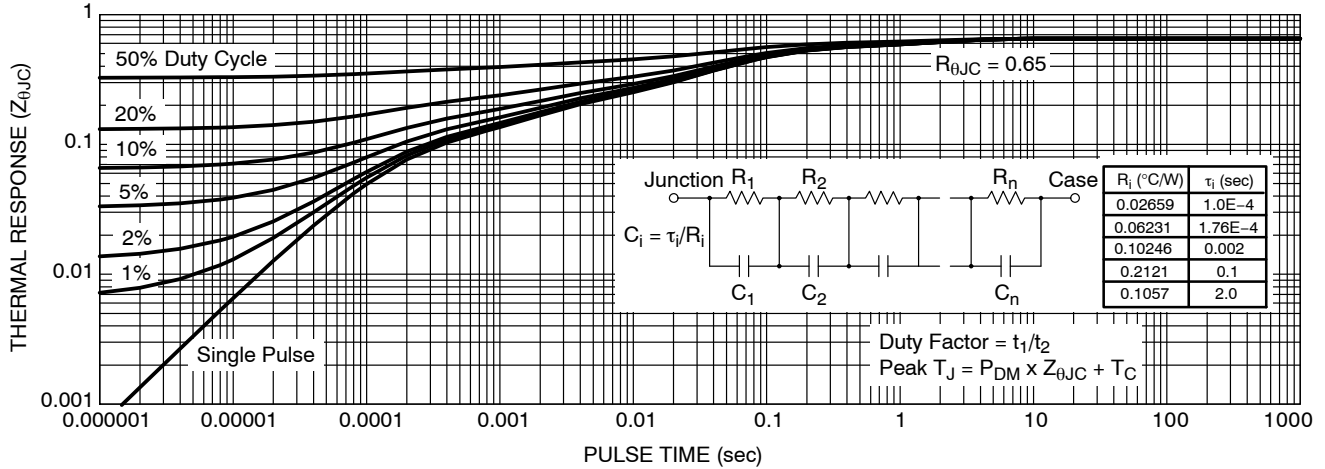


Figure 18. IGBT Transient Thermal Impedance

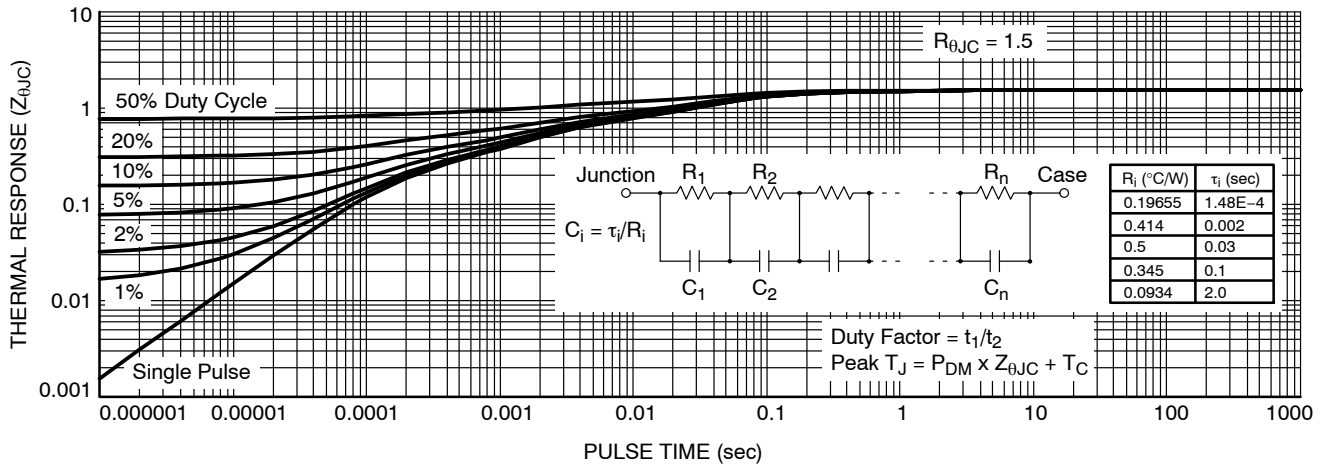


Figure 19. Diode Transient Thermal Impedance

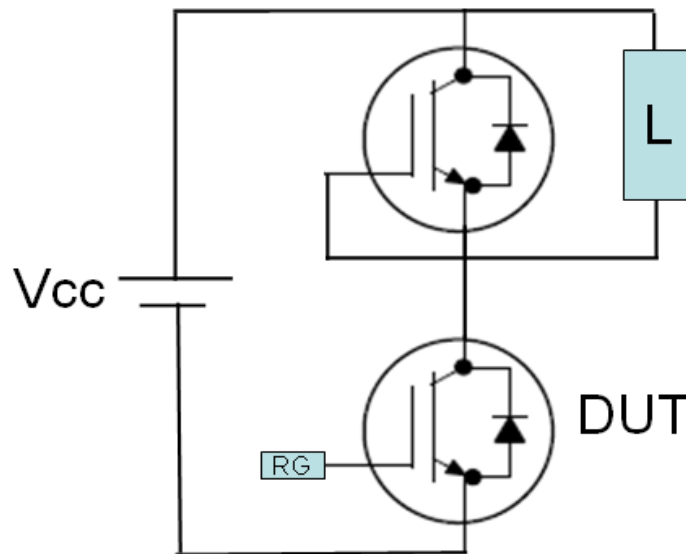


Figure 20. Test Circuit for Switching Characteristics

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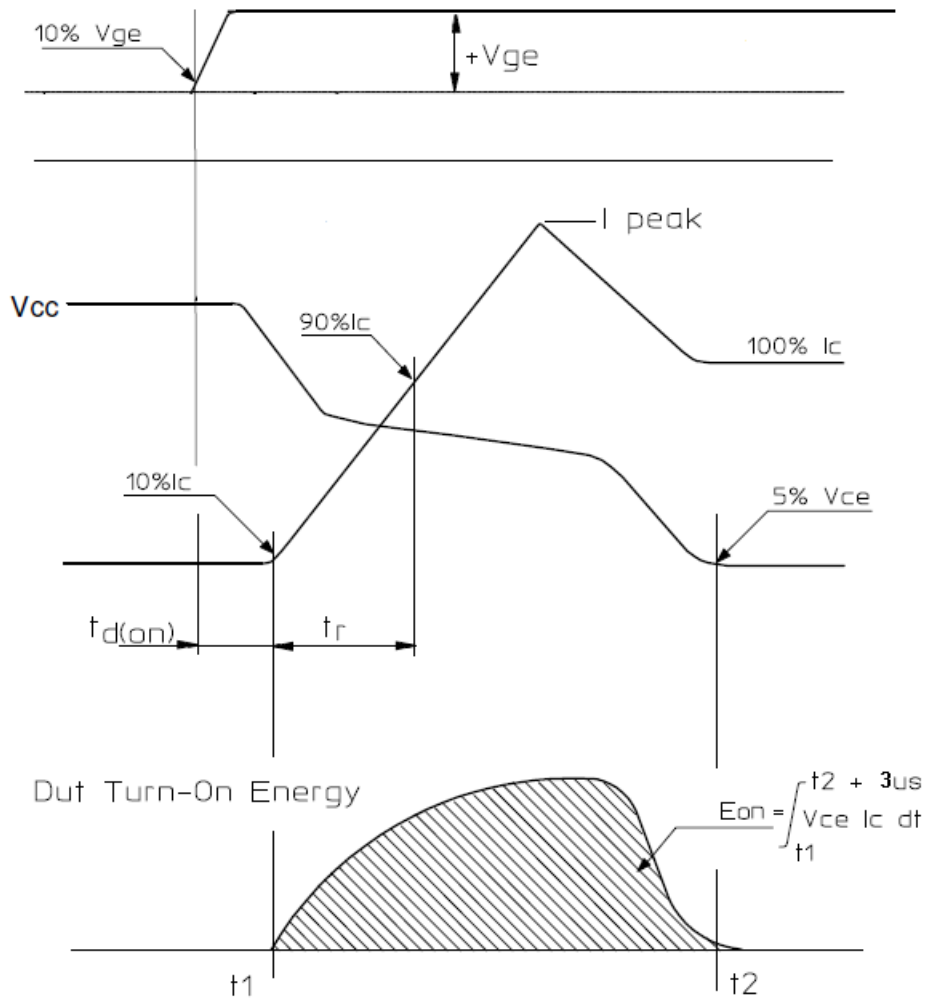


Figure 21. Definition of Turn On Waveform

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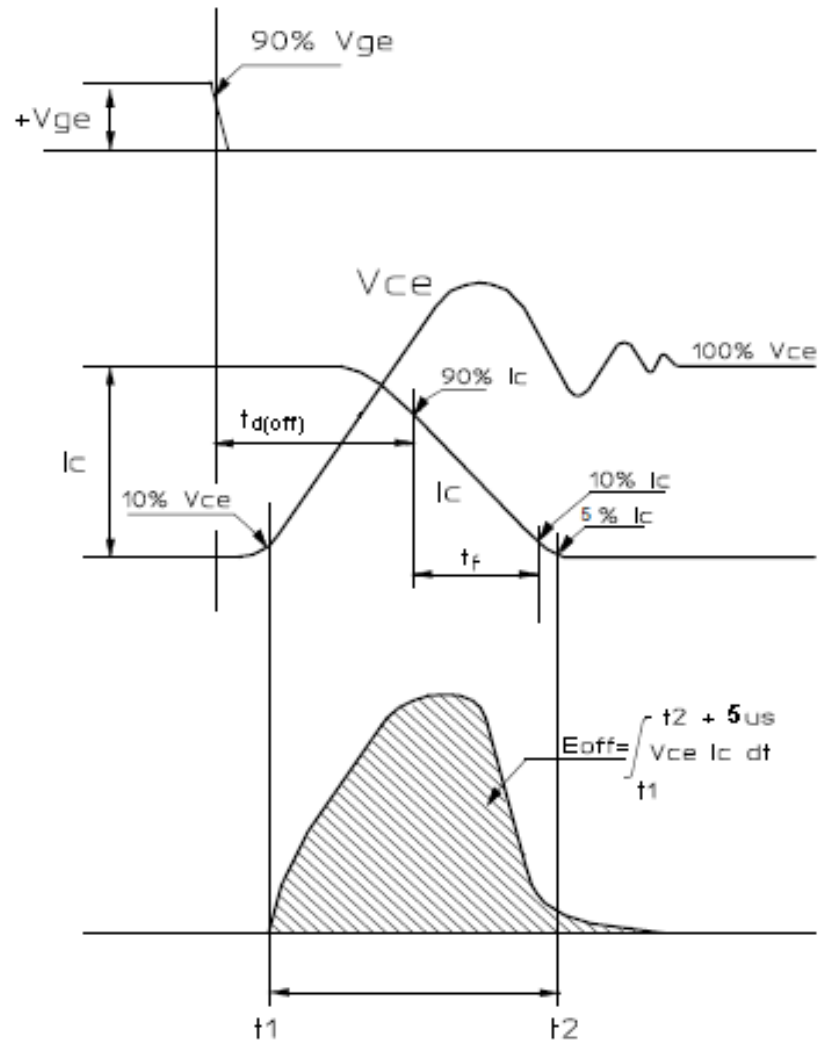


Figure 22. Definition of Turn Off Waveform